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20 V, single N-channel Trench MOSFET 13 November 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a SOT363 (SC-88) small Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|------------------------|----------------------------------|---|-----|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | - | 20 | V |
| V _{GS} | gate-source voltage | | | -8 | - | 8 | V |
| I _D | drain current | V_{GS} = 4.5 V; T_{amb} = 25 °C; t ≤ 5 s | [1] | - | - | 3.3 | А |
| Static characteristics | | | | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 4.5 V; I _D = 3 A; T _j = 25 °C | | - | 45 | 55 | mΩ |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





20 V, single N-channel Trench MOSFET

2. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | D | drain | 6 5 4 | D |
| 2 | D | drain | | |
| 3 | G | gate | | G UT 4 |
| 4 | S | source | ∐1 ∐2 ∐3 | S 017aaa253 |
| 5 | D | drain | TSSOP6 (SOT363) | 017444255 |
| 6 | D | drain | | |

3. Ordering information

| Table 3. Ordering information | | | | | |
|-------------------------------|--------|--|---------|--|--|
| Type number Package | | | | | |
| | Name | Description | Version | | |
| PMG45UN | TSSOP6 | plastic surface-mounted package; 6 leads | SOT363 | | |

4. Marking

| Table 4. Marking codes | |
|------------------------|--------------|
| Type number | Marking code |
| | [1] |
| PMG45UN | U5% |

[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| drain-source voltage | T _i = 25 °C | | | | _ |
|-------------------------|--|--|--|--|---|
| | J | | - | 20 | V |
| gate-source voltage | | | -8 | 8 | V |
| drain current | V_{GS} = 4.5 V; T_{amb} = 25 °C; t ≤ 5 s | [1] | - | 3.3 | А |
| | V _{GS} = 4.5 V; T _{amb} = 25 °C | [1] | - | 3 | А |
| | V _{GS} = 4.5 V; T _{amb} = 100 °C | [1] | - | 1.9 | А |
| peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$ | | - | 12 | А |
| total power dissipation | T _{amb} = 25 °C | [2] | - | 375 | mW |
| | | [1] | - | 715 | mW |
| - | drain current peak drain current total power dissipation | $\begin{array}{c} V_{GS} = 4.5 \text{ V}; \text{T}_{amb} = 25 ^{\circ}\text{C}; \text{t} \leq 5 \text{ s} \\ \hline V_{GS} = 4.5 \text{ V}; \text{T}_{amb} = 25 ^{\circ}\text{C} \\ \hline V_{GS} = 4.5 \text{ V}; \text{T}_{amb} = 100 ^{\circ}\text{C} \\ \hline \text{Peak drain current} \\ \end{array}$ | $\begin{array}{ c c c c c } \hline & & & & & & & & & & & & & & & & & & $ | $ \begin{array}{c c} \mbox{drain current} & V_{GS} = 4.5 \ V; \ T_{amb} = 25 \ ^{\circ}C; \ t \leq 5 \ s & [1] & - \\ \hline V_{GS} = 4.5 \ V; \ T_{amb} = 25 \ ^{\circ}C & [1] & - \\ \hline V_{GS} = 4.5 \ V; \ T_{amb} = 100 \ ^{\circ}C & [1] & - \\ \hline V_{GS} = 4.5 \ V; \ T_{amb} = 100 \ ^{\circ}C & [1] & - \\ \hline peak \ drain \ current & T_{amb} = 25 \ ^{\circ}C; \ single \ pulse; \ t_p \leq 10 \ \mu s & - \\ \hline total \ power \ dissipation & T_{amb} = 25 \ ^{\circ}C & [1] & - \\ \hline \hline 1 & - & \\ \hline \end{array} $ | $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ |

PMG45UN

20 V, single N-channel Trench MOSFET

| Symbol | Parameter | Conditions | | Min | Мах | Unit |
|------------------|----------------------|--------------------------|-----|-----|------|------|
| | | T _{sp} = 25 °C | | - | 4350 | mW |
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-dra | in diode | | | | | |
| I _S | source current | T _{amb} = 25 °C | [1] | - | 0.8 | А |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

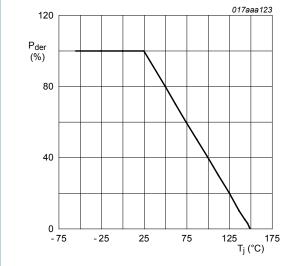


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

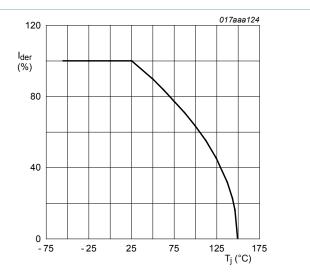
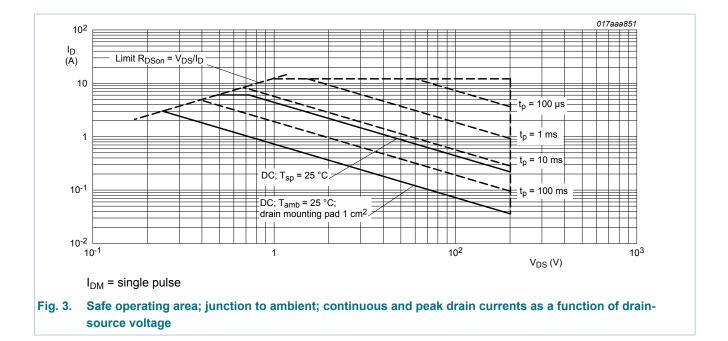


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100 \%$$

20 V, single N-channel Trench MOSFET



6. Thermal characteristics

| Table 6. The | rmal characteristics | | | | | | |
|---|--|-------------|-----|-----|-----|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| R _{th(j-a)} thermal resistance | | in free air | [1] | - | 289 | 332 | K/W |
| from junction to ambient | | | [2] | - | 152 | 175 | K/W |
| ampient | ambient | | [3] | - | 117 | 145 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 25 | 29 | K/W |

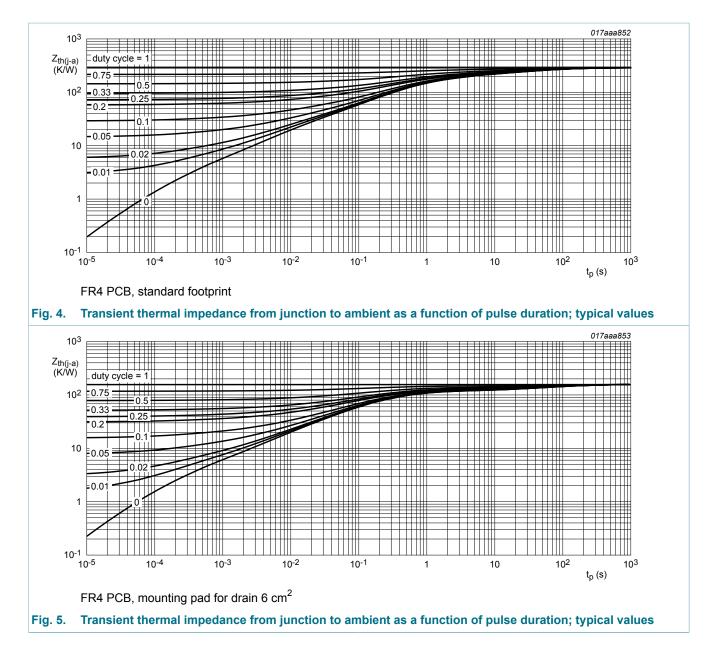
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm², t \leq 5 s.

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7. Characteristics

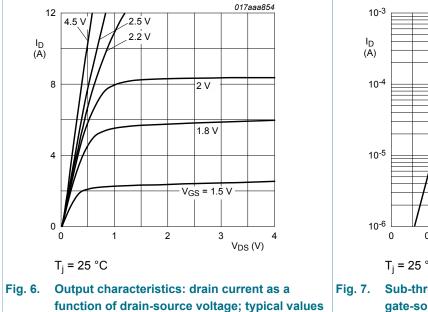
| Table 7. C | haracteristics | | | | | | |
|------------------------|-----------------------------------|---|--|-----|------|----------------|-------------------|
| Symbol | Parameter | Conditions | | Min | Тур | Мах | Unit |
| Static characteristics | | | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C | | 20 | - | - | V |
| V _{GSth} | gate-source threshold voltage | I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C | | 0.4 | 0.7 | 1 | V |
| I _{DSS} | drain leakage current | V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 °C | | - | - | 1 | μA |
| I _{GSS} | gate leakage current | V_{GS} = 8 V; V_{DS} = 0 V; T_j = 25 °C | | - | - | 100 | nA |
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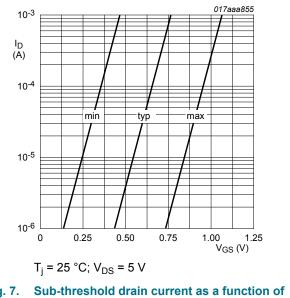
Product data sheet

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20 V, single N-channel Trench MOSFET

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|------------------------------|---|-----|------|------|------|
| | | V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -100 | nA |
| R _{DSon} | drain-source on-state | V _{GS} = 4.5 V; I _D = 3 A; T _j = 25 °C | - | 45 | 55 | mΩ |
| | resistance | V _{GS} = 4.5 V; I _D = 3 A; T _j = 150 °C | - | 66 | 81 | mΩ |
| | | V _{GS} = 2.5 V; I _D = 2.5 A; T _j = 25 °C | - | 58 | 76 | mΩ |
| | | V _{GS} = 1.8 V; I _D = 0.8 A; T _j = 25 °C | - | 85 | 125 | mΩ |
| 9 _{fs} | forward transconductance | V _{DS} = 10 V; I _D = 3 A; T _j = 25 °C | - | 11.2 | - | S |
| Dynamic c | haracteristics | | | | | |
| Q _{G(tot)} | total gate charge | V_{DS} = 10 V; I _D = 3 A; V _{GS} = 4.5 V; | - | 2.2 | 3.3 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 0.32 | - | nC |
| Q _{GD} | gate-drain charge | | - | 0.56 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V; | - | 184 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 51 | - | pF |
| C _{rss} | reverse transfer capacitance | _ | - | 29 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 10 V; I _D = 3 A; V _{GS} = 4.5 V; | - | 8 | - | ns |
| t _r | rise time | R _{G(ext)} = 6 Ω; T _j = 25 °C | - | 30 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 30 | - | ns |
| t _f | fall time | | - | 26 | - | ns |
| Source-dra | iin diode | · | | | | |
| V _{SD} | source-drain voltage | I_{S} = 0.8 A; V_{GS} = 0 V; T_{j} = 25 °C | - | 0.8 | 1.2 | V |

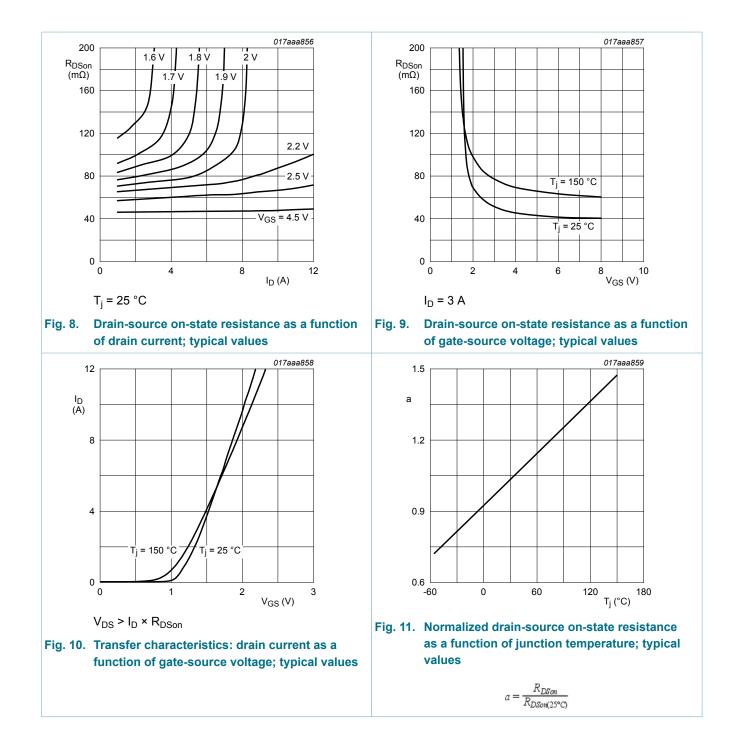




gate-source voltage

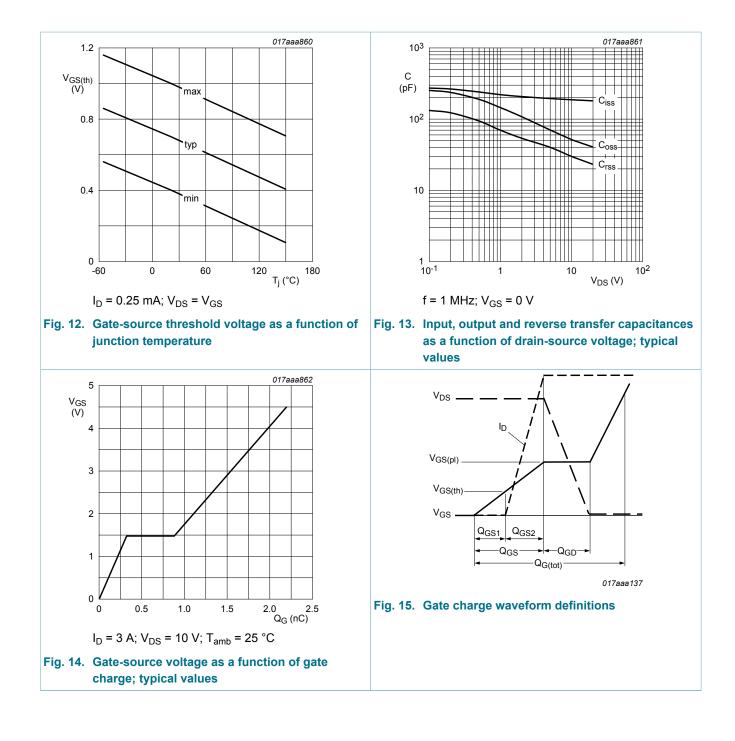
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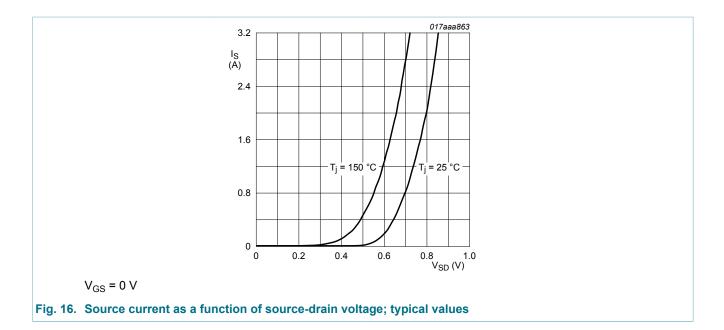
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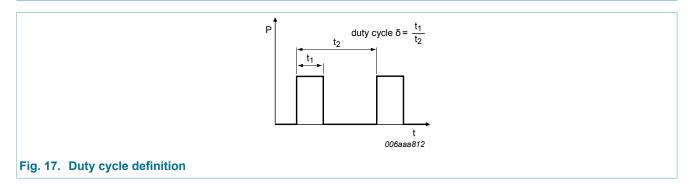


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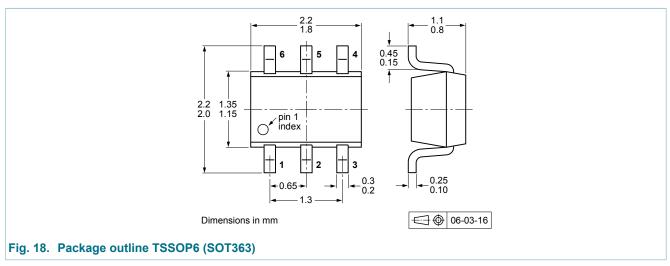
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8. Test information

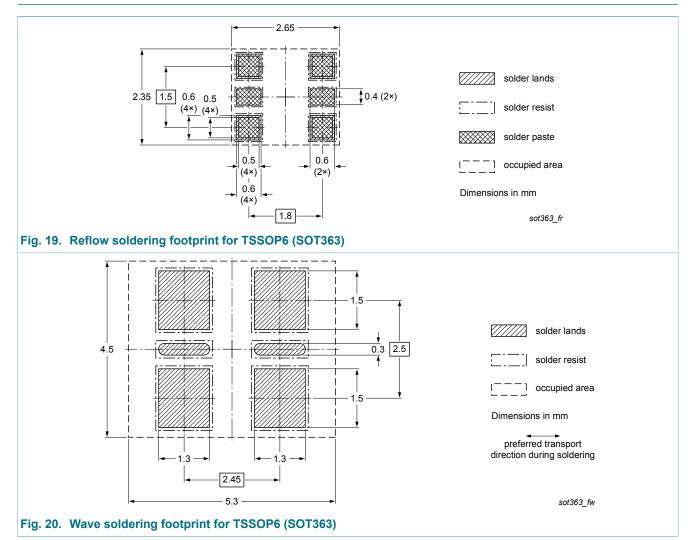


9. Package outline



20 V, single N-channel Trench MOSFET

10. Soldering



11. Revision history

| Table 8. Revision history | | | | | |
|-------------------------------|--------------|--------------------|---------------|------------|--|
| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | |
| PMG45UN v.1 | 20121113 | Product data sheet | - | - | |

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20 V, single N-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

| Document status [1][2] | Product status [<u>3]</u> | Definition |
|--------------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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